TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

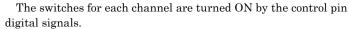
TC7MZ4051FK,TC7MZ4052FK,TC7MZ4053FK

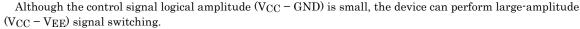
TC7MZ4051FK 8-Channel Analog Multiplexer/Demultiplexer TC7MZ4052FK Dual 4-Channel Analog Multiplexer/Demultiplexer

TC7MZ4053FK Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC7MZ4051/4052/4053FK are high-speed, low-voltage drive analog multiplexer/demultiplexers using silicon gate CMOS technology. In 3 V and 5 V systems these can achieve high-speed operation with the low power dissipation that is a feature of CMOS.

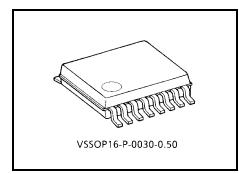
The TC7MZ4051/4052/4053FK offer analog/digital signal selection as well as mixed signals. The 4051 has an 8-channel configuration, the 4052 has an 4-channel \times 2 configuration, and the 4053 has a 2-channel \times 3 configuration.





For example, if $V_{CC} = 3 \text{ V}$, GND = 0 V, and $V_{EE} = -3 \text{ V}$, signals between -3 V and +3 V can be switched from the logical circuit using a single 3 V power supply.

All input pins are equipped with a newly developed input protection circuit that avoids the need for a diode on the plus side (forward side from the input to the VCC). As a result, for example, 5 V signals can be permitted on the inputs even when the power supply voltage to the circuits is off. As a result of this input power protection, the TC7MZ4051/4052/4053FK can be used in a variety of applications, including in the system which has two power supplies, and in battery backup circuits.



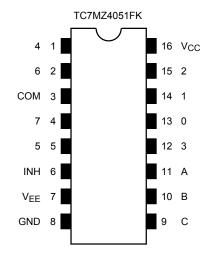
Weight: 0.02 g (typ.)

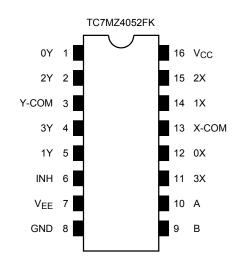
Features

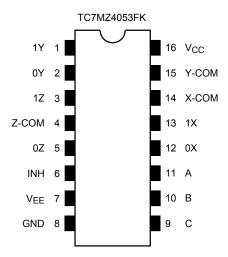
- Low ON resistance: $R_{on} = 22 \Omega \text{ (typ.)} \text{ (V}_{CC} \text{V}_{EE} = 3 \text{ V)}$ $R_{on} = 15 \Omega \text{ (typ.)} \text{ (V}_{CC} - \text{V}_{EE} = 6 \text{ V)}$
- High speed: $t_{pd} = 3 \text{ ns (typ.) (VCC} = 3.0 \text{ V)}$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- Input level: V_{IL} = 0.8 V (max) (V_{CC} = 3 V) V_{IH} = 2.0 V (min) (V_{CC} = 3 V)
- Power down protection is provided on all control inputs
- Pin and function compatible with 74HC4051/4052/4053



Pin Assignment (top view)







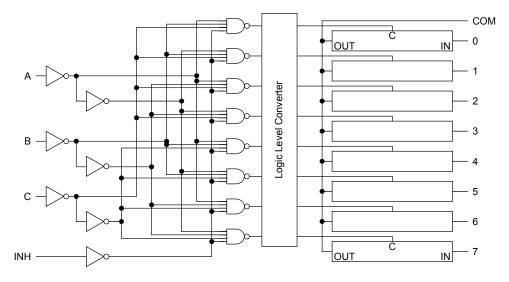
Truth Table

	Contro	Inputs		"ON" Channel				
Inhibit	C*	В	А	MZ4051FK	MZ4051FK MZ4052FK			
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	_	0X, 0Y, 1Z		
L	Н	L	Н	5	_	1X, 0Y, 1Z		
L	Н	Н	L	6	_	0X, 1Y, 1Z		
L	Н	Н	Н	7	_	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

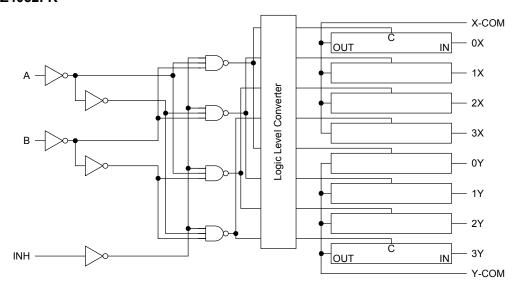
X: Don't care, *: Except MZ4052FK

System Diagram

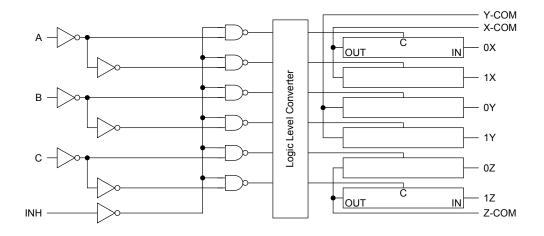
TC7MZ4051FK



TC7MZ4052FK



TC7MZ4053FK





Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5~7.0	V
r ower supply voltage	V _{CC} ~V _{EE}	-0.5~7.0	V
Control input voltage	V _{IN}	-0.5~7.0	V
Switch I/O voltage	V _{I/O}	V _{EE} - 0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
I/O diode current	l _{IOK}	±20	mA
Switch through current	I _T	±25	mA
DC V _{CC} or ground current	I _{CC}	±50	mA
Power dissipation	PD	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit
	V _C C	2~6	
Power supply voltage	V _{EE}	-4~0	V
	V _{CC} ~V _{EE}	2~6	
Input voltage	V _{IN}	0~6.0	V
Switch I/O voltage	V _{I/O}	V _{EE} ~V _{CC}	V
Operating temperature	T _{opr}	-40~85	°C
Input rise and fall time	dt/dv	0~100 (V _{CC} = 3.3 ± 0.3 V)	ns/V
input noe and fall time	uuuv	0~20 (V _{CC} = 5 ± 0.5 V)	ris/V

Note: The operating ranges must be maintained to ensure the normal operation of the device.

Unused control inputs must be tied to either V_{CC} or GND.



Electrical Characteristics

DC Electrical Characteristics

Characteristics		Symbol	ol Test Condition			•	Га = 25°()	Ta = -40~85°C		Unit
		Syllibol	rest Condition	V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Min	Max	OTILL
					2.0	1.5	_	_	1.5	_	
	High-level	V _{IH}			3.0	2.0	_	_	2.0	_	
	riigii-level	VIH	_		4.5	3.15	_	_	3.15	_	
Input voltage					6.0	4.2	_	_	4.2	_	V
input voitage					2.0	_	_	0.5	_	0.5	V
	Low-level	V _{IL}			3.0	_	_	0.8	_	0.8	
	Low-level	V IL	_		4.5	_	_	1.35	_	1.35	
					6.0		_	1.8	_	1.8	
			\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	GND	2.0	_	200	_	_	_	
			$V_{IN} = V_{IL}$ or V_{IH} $V_{I/O} = V_{CC}$ to V_{EE} $I_{I/O} = 2$ mA	GND	3.0		45	86	_	108	Ω
				GND	4.5		24	37	_	46	
ON resistance		R _{ON}		-3.0	3.0	_	17	26	_	33	
ON Tesistatice		NON		GND	2.0	_	28	73	_	84	
			$\begin{split} V_{IN} &= V_{IL} \text{ or } V_{IH} \\ V_{I/O} &= V_{CC} \text{ or } V_{EE} \\ I_{I/O} &= 2 \text{ mA} \end{split}$	GND	3.0	_	22	38	_	44	
				GND	4.5	_	17	27	_	31	
				-3.0	3.0	_	15	24	_	28	
		ΔR _{ON} V _{I/O}	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	GND	2.0		10	25	_	35	Ω
Difference of O resistance betw			$\begin{aligned} &V_{IN} = V_{IL} \text{ or } V_{IH} \\ &V_{I/O} = V_{CC} \text{ to } V_{EE} \\ &I_{I/O} = 2 \text{ mA} \end{aligned}$	GND	3.0	_	5	15	_	20	
switches	/een			GND	4.5	_	5	13	_	18	
				-3.0	3.0		5	10	_	15	
Input/Output lea	akage		$V_{OS} = V_{CC}$ or GND	GND	3.0		_	±0.25	_	±2.5	
current (switch OFF)		l _{OFF}	$V_{IS} = GND \text{ to } V_{CC}$ $V_{IN} = V_{IL} \text{ or } V_{IH}$	-3.0	3.0		_	±0.5	_	±5.0	μΑ
Input/Output leakage		V _{OS} = V _{CO}	V _{OS} = V _{CC} or GND	GND	3.0	_	_	±0.25	_	±2.5	
current (switch ON, out	put open)	I _{IN}	$V_{IN} = V_{IL}$ or V_{IH}	-3.0	3.0		_	±0.5	_	±5.0	μΑ
Control input cu	ırrent	I _{IN}	V _{IN} = V _{CC} or GND	GND	6.0	_	_	±0.1	_	±0.1	μΑ
Outoposet sure	hy ourrest			GND	3.0			4.0	_	40.0	^
Quiescent supp	ny current	Icc	$V_{IN} = V_{CC}$ or GND	-3.0	3.0	_	_	8.0	_	80.0	μА



AC Electrical Characteristics ($C_L = 50 \text{ pF}$, Input: $t_r = t_f = 3 \text{ ns}$, GND = 0 V)

Characteristics	Cumbal	Symbol Test Condition					Ta = 25°C			Ta = -40~85°C	
Characteristics	Symbol			V _{EE} (V)	V _{CC} (V)	Min	Тур.	Max	Min	Max	Unit
				GND	2.0	_	3.2	6.0	_	6.9	ns
Phase difference between	φI/O	All type	All types		3.0	_	1.8	3.0	_	3.5	
input and output	ψι/Ο	All types		GND	4.5		1.3	1.8	_	2.1	115
				-3.0	3.0		1.1	1.3	_	1.5	
				GND	2.0		9.0	17	_	20	
Output enable time	t _{pZL}	Figure	1 (Note 1)	GND	3.0		5.7	9.0	_	11	ne
Output enable time	t _p ZH	i igui e	i (Note i)	GND	4.5		4.5	6.0	_	7.0	ns
				-3.0	3.0		5.8	8.0	_	10	
				GND	2.0		13.5	21	_	25	- ns
Output disable time	t _{pLZ}	Figure 1	1 (Note 1)	GND	3.0		11.3	15	_	18	
Output disable time	t _{pHZ}		(Note 1)	GND	4.5		10.3	12	_	14	
				-3.0	3.0		10.9	13	_	15	
Control input capacitance	C _{in}	All type	es (Note 2)	_			5	10	_	10	pF
		4051	Figure 2 (Note 2)				11	25		25	
COMMON terminal capacitance	C _{IS}	4052		-3.0	3.0	_	9	20		20	pF
		4053					7	15		15	
		4051					6	13		13	
SWITCH terminal capacitance	Cos	4052	Figure 2 (Note 2)	-3.0	3.0	_	6	13	_	13	pF
		4053	(14016-2)				6	13		13	
		4051					3	6		6	
Feedthrough capacitance	C _{IOS}	4052	Figure 2 (Note 2)	-3.0	3.0	_	3	6	_	6	pF
		4053					3	6		6	
		4051					14				
Power dissipation capacitance	C_{PD}	4052	Figure 2 (Note 3)	GND	6.0	_	24	_	_	_	pF
		4053					18				

Note 1: $R_L = 1 k\Omega$

Note 2: C_{in} , C_{IS} , C_{OS} and C_{IOS} are guaranteed by the design.

Note 3: C_{PD} is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

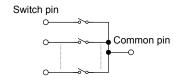
 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$



*Analog Switch Characteristics (GND = 0 V, Ta = 25°C)

Characteristics	Symbol	Test Condition			Тур.	Unit	
Characteristics	Gyiriboi	rest oblidition		V _{EE} (V)	V _{CC} (V)	τyp.	Offic
			$V_{IN}=2.0\;V_{p\text{-}p}$	0	3.0	0.100	%
Sine Wave Distortion (T.H.D)		$R_L = 10 \text{ k}\Omega, C_L = 50 \text{ pF},$ $f_{IN} = 1 \text{ kHz}$	$V_{IN} = 4.0 V_{p-p}$	0	4.5	0.030	
			$V_{IN}=6.0\;V_{p\text{-}p}$	-0.3	3.0	0.020	
			4051			150	
			4052	0	3.0	180	MHz
		Adjust f _{IN} voltage to obtain 0dBm at V _{OS} .	4053			200	
Frequency response		Increase f _{IN} frequency until dB	4051			150	
(switch ON)	f _{max}	meter reads –3dB.	4052	0	4.5	180	
(SWILCH OIV)		$R_L = 50 \Omega$, $C_L = 10 pF$, $f_{IN} = 1 MHz$, sine wave	4053			200	
		Figure 3	4051		3.0	150	
			4052	-3.0		180	
			4053			200	
		V _{IN} is centered at (V _{CC} – V _{EE})/2.	0	3.0	-45	dB	
		Adjust input for 0dBm.	0	4.5	–45		
		$R_L = 600 \ \Omega$, $C_L = 50 \ pF$, $f_{IN} = 1 \ M$	-		-40		
Feed through attenuation (switch OFF)		Figure 4	-3.0	3.0	-45		
			0	3.0	-60		
		$R_L = 50~\Omega,~C_L = 10~pF,~f_{\mbox{\footnotesize{IN}}} = 1~\mbox{\footnotesize{MHz}},~\mbox{\footnotesize{sine}}$ wave		0	4.5		-60
				-3.0	3.0	-60	
Crosstalk		$R_L = 600 \ \Omega$, $C_L = 50 \ pF$, $f_{IN} = 1 \ M$	Hz, square wave	0	3.0	90	
(control input to signal		$(t_{\Gamma}=t_{f}=6 \text{ ns})$	0	4.5	150	mV	
output)		Figure 5		-3.0	3.0	120	
Crosstalk		Adjust V _{IN} to obtain 0dBm at inpu	0	3.0	-45		
(between any switches)		$R_L = 600 \ \Omega, \ C_L = 50 \ pF, \ f_{IN} = 1 \ M$	0	4.5	-45	dB	
(between any switches)		Figure 6		-3.0	3.0	-45	

*: These characteristics are determined by design of devices.



AC Test Circuit

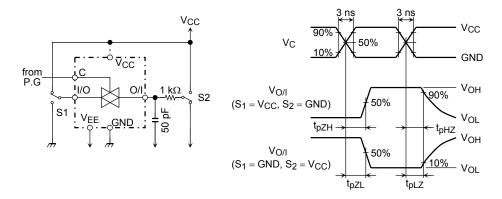


Figure 1 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH}

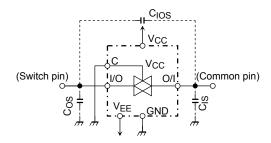


Figure 2 C_{IOS}, C_{IS}, C_{OS}

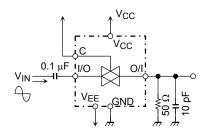


Figure 3 Frequency Response (switch on)

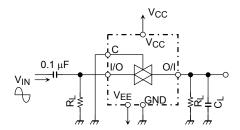


Figure 4 Feedthrough

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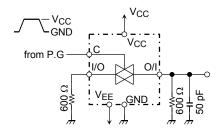


Figure 5 Cross Talk (control input to output signal)

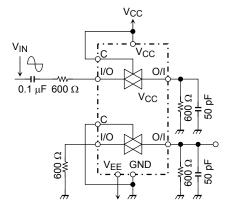
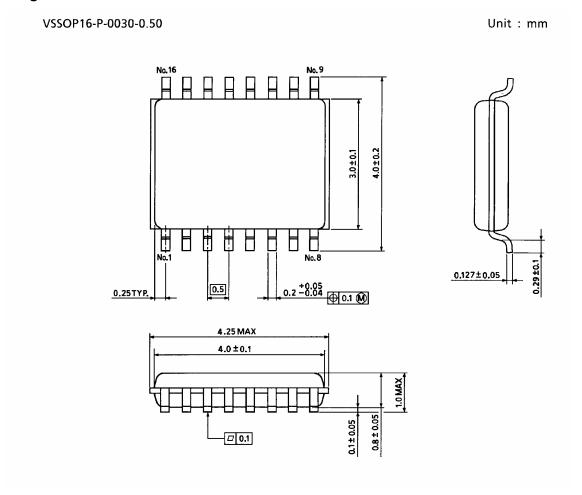


Figure 6 Cross Talk (between any two switches)



Package Dimensions



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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